

## HIGH FREQUENCY HALF-BRIDGE GATE DRIVER WITH PROGRAMMABLE DEADTIME

### Description

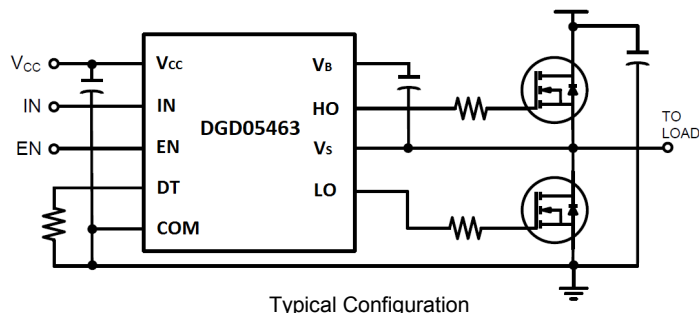
The DGD05463 is a high-frequency half-bridge gate driver capable of driving N-channel MOSFETs in a half-bridge configuration. The floating high-side driver is rated up to 50V.

The DGD05463 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with MCUs. UVLO for high-side and low-side will protect a MOSFET with loss of supply. To protect MOSFETs, cross conduction prevention logic prevents the HO and LO outputs being on at the same time.

Fast and well-matched propagation delays allow a higher switching frequency, which enable a smaller, more compact power switching design using smaller associated components. The DGD05463 is offered in the W-DFN3030-10 and MSOP-10 packages and operates over an extended -40°C to +125°C temperature range.

### Applications

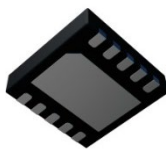
- DC-DC Converters
- Motor Controls
- Battery Powered Hand Tools
- eCig Devices
- Class-D Power Amplifiers



W-DFN3030-10



Top View



Bottom View

MSOP-10



Top View

### Features

- 50V Floating High-Side Driver
- Drives Two N-Channel MOSFETs in a Half-Bridge Configuration
- 1.5A Source / 2.5A Sink Output Current Capability
- Internal Bootstrap Diode Included
- Undervoltage Lockout for High-Side and Low-Side Drivers
- Programmable Deadtime to Protect MOSFETs
- Logic Input (IN and EN) 3.3V Capability
- Ultra-Low Standby Currents (<1μA)
- Extended Temperature Range: -40°C to +125°C
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative.**

<https://www.diodes.com/quality/product-definitions/>

### Mechanical Data

- Case: W-DFN3030-10 (Type TH), MSOP-10
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish – Matte Tin Finish. Solderable per MIL-STD-202, Method 208
- Weight:
  - W-DFN3030-10: 0.017 grams (Approximate)
  - MSOP-10: 0.0286 grams (Approximate)

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

## Ordering Information (Note 4)

Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DGD05463FN-7	W-DFN3030-10	DGD05463	7	8	3000
DGD05463M10-13	MSOP-10	DGD05463	13	12	2500

Note: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

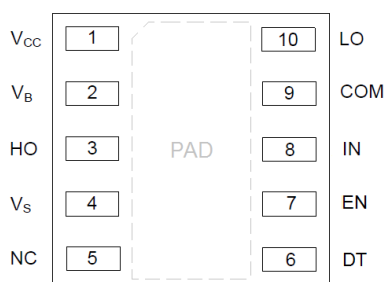


DGD05463 = Product Type Marking Code  
 YY = Year (ex: 21 = 2021)  
 WW = Week (01 to 53)

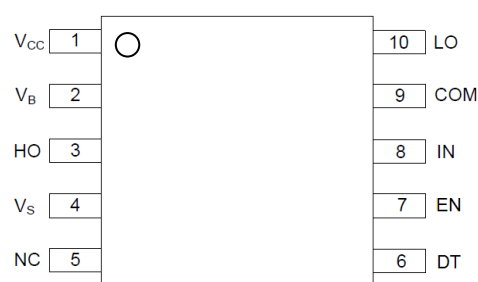


⌋⌋⌋ = Manufacturer's Code Marking  
 DGD05463 = Product Type Marking Code  
 Y = Year: 0 ~ 9  
 W = Week: A ~ Z : 1 ~ 26 week  
 a ~ z : 27 ~ 52 week

## Pin Diagrams



Top View: W-DFN3030-10

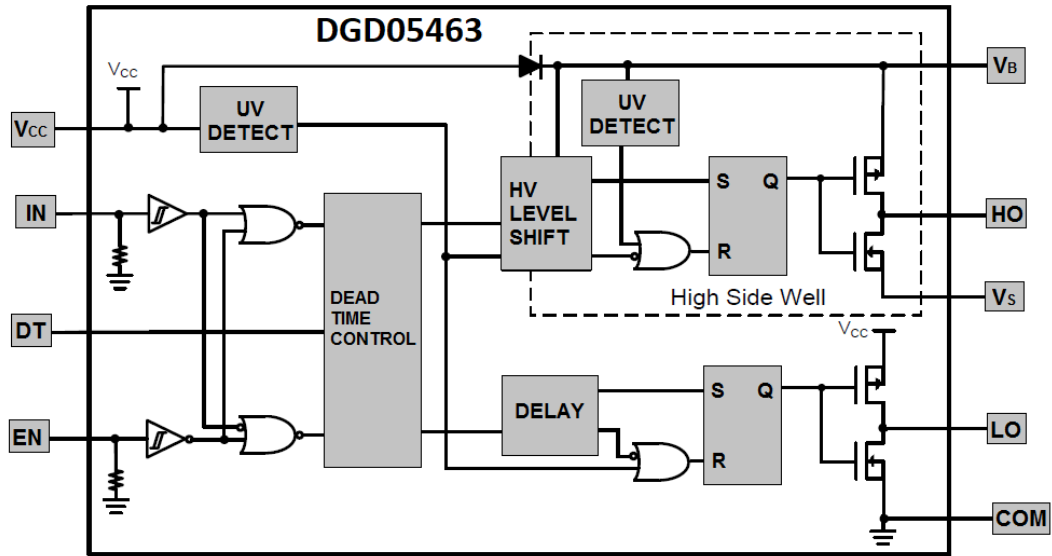


Top View: MSOP-10

## Pin Descriptions

Pin Number	Pin Name	Function
1	V <sub>CC</sub>	Low-Side and Logic Supply
2	V <sub>B</sub>	High-Side Floating Supply
3	HO	High-Side Gate Drive Output
4	V <sub>S</sub>	High-Side Floating Supply Return
5	NC	No Connection (No Internal Connection)
6	DT	Deadtime Control
7	EN	Logic Input Enable, a Logic Low Turns Off Gate Driver
8	IN	Logic Input for High-Side and Low-Side Gate Driver Outputs (HO and LO), in Phase with HO
9	COM	Low-Side and Logic Return
10	LO	Low-Side Gate Drive Output
PAD	Substrate	Connect to COM on PCB (For W-DFN3030-10 Only)

**Functional Block Diagram**



**Absolute Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Positive Supply Voltage	$V_B$	-0.3 to +60	V
High-Side Floating Negative Supply Voltage	$V_S$	$V_B - 14$ to $V_B + 0.3$	V
High-Side Floating Output Voltage	$V_{HO}$	$V_S - 0.3$ to $V_B + 0.3$	V
Offset Supply Voltage Transient	$dV_S / dt$	50	V/ns
Logic and Low-Side Fixed Supply Voltage	$V_{CC}$	-0.3 to +14	V
Low-Side Output Voltage	$V_{LO}$	-0.3 to $V_{CC} + 0.3$	V
Logic Input Voltage (IN and EN)	$V_{IN}$	-0.3 to $V_{CC} + 0.3$	V

**Thermal Characteristics – W-DFN3030-10** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	$P_D$	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	64	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case (Note 5)	$R_{\theta JC}$	42	$^\circ\text{C}/\text{W}$
Operating Temperature	$T_J$	+150	$^\circ\text{C}$
Lead Temperature (Soldering, 10s)	$T_L$	+300	
Storage Temperature Range	$T_{STG}$	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

**Thermal Characteristics – MSOP-10** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 6)	$P_D$	0.75	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	166	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	32	$^\circ\text{C}/\text{W}$
Operating Temperature	$T_J$	+150	$^\circ\text{C}$
Lead Temperature (Soldering, 10s)	$T_L$	+300	
Storage Temperature Range	$T_{STG}$	-55 to +150	

Note: 6. When mounted on a standard JEDEC 2-layer FR-4 board with minimum recommended pad layout.

**Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply	$V_B$	$V_S + 4.2$	$V_S + 14$	V
High-Side Floating Supply Offset Voltage	$V_S$	(Note 7)	50 (Note 8)	V
High-Side Floating Output Voltage	$V_{HO}$	$V_S$	$V_B$	V
Logic and Low-Side Fixed Supply Voltage	$V_{CC}$	4.5 (Note 9)	14	V
Low-Side Output Voltage	$V_{LO}$	0	$V_{CC}$	V
Logic Input Voltage (IN and EN)	$V_{IN}$	0	5	V
Ambient Temperature	$T_A$	-40	+125	$^\circ\text{C}$

Notes: 7. Logic operation for  $V_S$  of -5V to +50V.

8. Provided  $V_B$  doesn't exceed absolute maximum rating of 60V.

9. For operation of  $V_{CC} = 4.5\text{V}$  to  $4.9\text{V}$ , an external bootstrap Schottky diode ( $0.3\text{V } V_{FD}$ , 1A) is necessary, as shown in Figure 3. For operation  $V_{CC} \geq 4.9\text{V}$ , the external Schottky diode is not required.

**DC Electrical Characteristics** ( $V_{CC} = V_{BS} = 12V$ ,  $COM = V_S = 0V$ , @  $T_A = +25^\circ C$ , unless otherwise specified.) (Note 10)

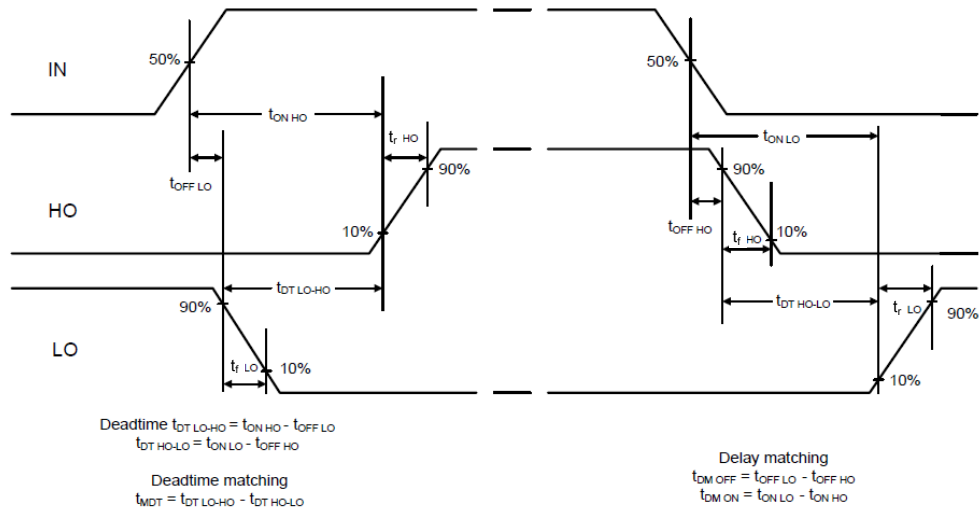
Parameter	Symbol	Min	Typ	Max	Unit	Condition
Logic "1" Input Voltage	$V_{IH}$	2.4	—	—	V	—
Logic "0" Input Voltage	$V_{IL}$	—	—	0.8	V	—
Enable Logic "1" Input Voltage	$V_{ENIH}$	1.5	—	—	V	—
Enable Logic "0" Input Voltage	$V_{ENIL}$	—	—	0.7	V	—
Input Voltage Hysteresis	$V_{INHYS}$	—	0.6	—	V	—
High Level Output Voltage, $V_{BIAS} - V_O$	$V_{OH}$	—	0.45	0.6	V	$I_{O+} = 100mA$
Low Level Output Voltage, $V_O$	$V_{OL}$	—	0.15	0.22	V	$I_{O-} = 100mA$
Offset Supply Leakage Current	$I_{LK}$	—	10	50	$\mu A$	$V_B = V_S = 60V$
$V_{CC}$ Shutdown Supply Current	$I_{CCSD}$	—	0	1	$\mu A$	$V_{IN} = 0V$ or $5V$ , $V_{EN} = 0V$
$V_{CC}$ Quiescent Supply Current	$I_{CCQ}$	—	0.28	0.5	mA	$V_{IN} = 0V$ or $5V$ , $R_{DT} = 100k\Omega$
$V_{CC}$ Operating Supply Current	$I_{CCOP}$	—	7.6	—	mA	$f_s = 500kHz$ , $C_L = 1000pF$
$V_{BS}$ Quiescent Supply Current	$I_{BSQ}$	—	32	100	$\mu A$	$V_{IN} = 0V$ or $5V$
$V_{BS}$ Operating Supply Current	$I_{BSOP}$	—	7.6	—	mA	$f_s = 500kHz$ , $C_L = 1000pF$
Logic "1" Input Bias Current	$I_{IN+}$	—	25	60	$\mu A$	$V_{IN} = 5V$
Logic "0" Input Bias Current	$I_{IN-}$	—	0	1	$\mu A$	$V_{IN} = 0V$
$V_{BS}$ Supply Undervoltage Positive Going Threshold	$V_{BSUV+}$	3.3	3.8	4.2	V	—
$V_{BS}$ Supply Undervoltage Negative Going Threshold	$V_{BSUV-}$	2.9	3.3	3.9	V	—
$V_{CC}$ Supply Undervoltage Positive Going Threshold	$V_{CCUV+}$	3.3	3.8	4.2	V	—
$V_{CC}$ Supply Undervoltage Negative Going Threshold	$V_{CCUV-}$	2.9	3.3	3.9	V	—
Output High Short-Circuit Pulsed Current	$I_{O+}$	1.0	1.5	—	A	$V_O = 0V$ , $PW \leq 10\mu s$
Output Low Short-Circuit Pulsed Current	$I_{O-}$	1.9	2.5	—	A	$V_O = 15V$ , $PW \leq 10\mu s$
Forward Voltage of Bootstrap Diode	$V_{F1}$	—	0.67	—	V	$I_F = 100\mu A$
Forward Voltage of Bootstrap Diode	$V_{F2}$	—	1.7	—	V	$I_F = 100mA$

Note: 10. The  $V_{IN}$  and  $I_{IN}$  parameters are applicable to the two logic pins: IN and EN. The  $V_O$  and  $I_O$  parameters are applicable to the respective output pins: HO and LO.

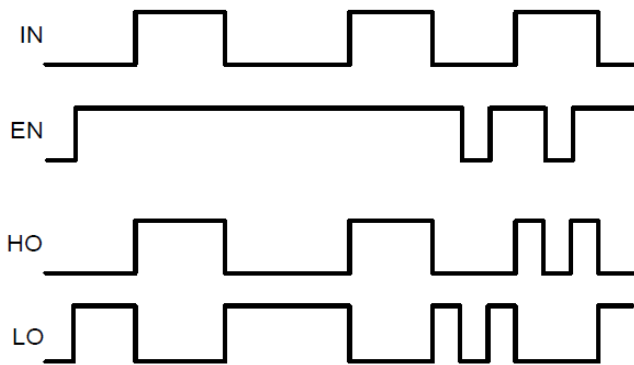
**AC Electrical Characteristics** ( $V_{CC} = V_{BS} = 12V$ ,  $COM = V_S = 0V$ ,  $C_L = 1000pF$ , @  $T_A = +25^\circ C$ , unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Turn-on Propagation Delay, HO & LO	$t_{ON}$	65	96	125	ns	$R_{DT} = 10k\Omega$
		350	463	580	ns	$R_{DT} = 100k\Omega$
Turn-off Propagation Delay, HO & LO	$t_{OFF}$	—	22	56	ns	—
Turn-on Rise Time	$t_r$	—	17	35	ns	—
Turn-off Fall Time	$t_f$	—	12	25	ns	—
Delay Matching	$t_{DM}$	—	—	50	ns	—
Deadtime: $t_{DT LO-HO}$ & $t_{DT HO-LO}$	$t_{DT}$	40	70	100	ns	$R_{DT} = 10k\Omega$
		300	430	560	ns	$R_{DT} = 100k\Omega$
Deadtime Matching	$t_{MDT}$	—	—	50	ns	$R_{DT} = 100k\Omega$

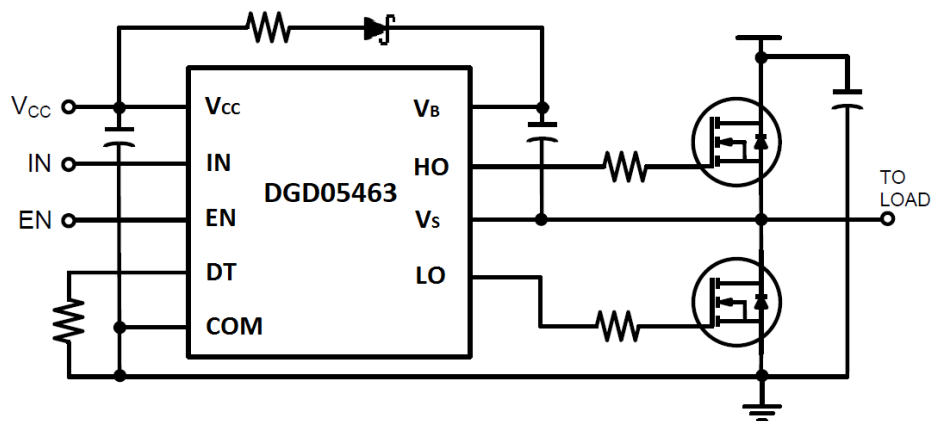
**Timing Waveforms**



**Figure 1.** Switching Time Waveform Definitions



**Figure 2.** Input / Output Timing Diagram



**Figure 3.** Typical application necessary for  $V_{CC} = 4.5V$  to  $4.9V$  operation. For  $V_{CC} \geq 4.9V$ , the bootstrap Schottky diode (0.3V Voltage drop, 1A) and resistor are not required.

**Typical Performance Characteristics** ( $V_{CC} = 12V$ , @  $T_A = +25^\circ C$ , unless otherwise specified.)

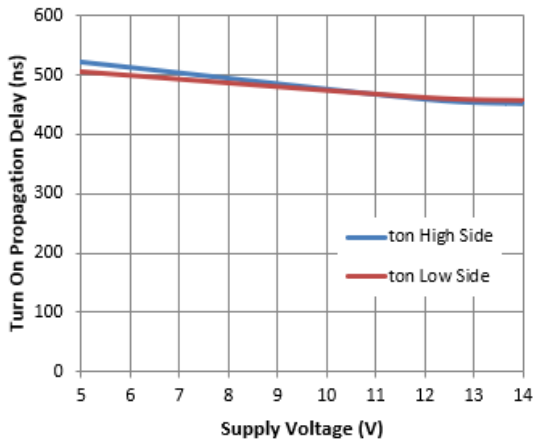


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

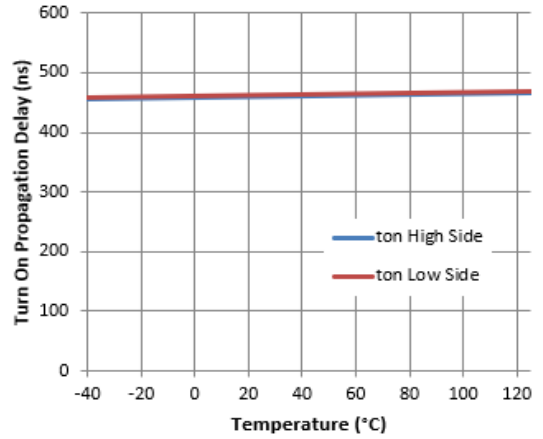


Figure 5. Turn-on Propagation Delay vs. Temperature

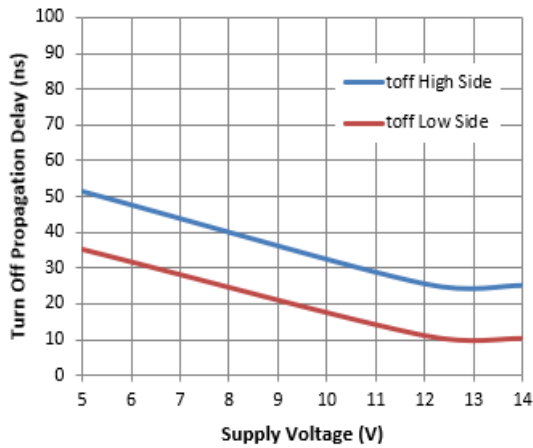


Figure 6. Turn-off Propagation Delay vs. Supply Voltage

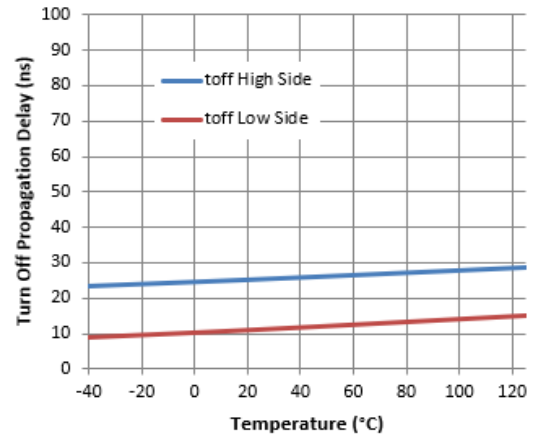


Figure 7. Turn-off Propagation Delay vs. Temperature

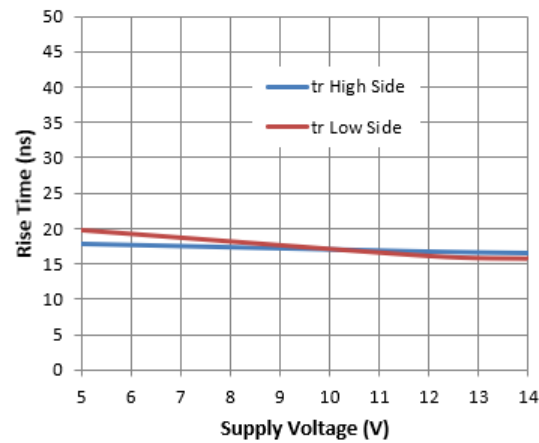


Figure 8. Rise Time vs. Supply Voltage

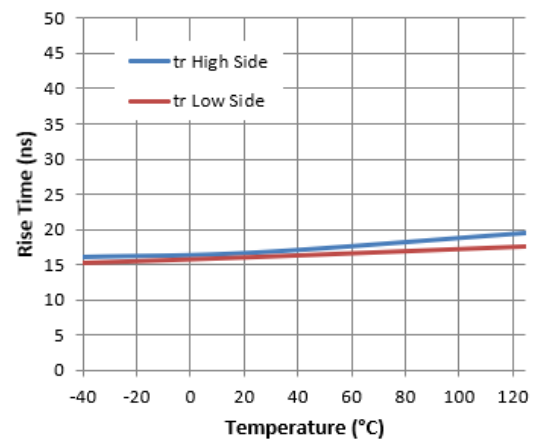


Figure 9. Rise Time vs. Temperature

**Typical Performance Characteristics** (continued)

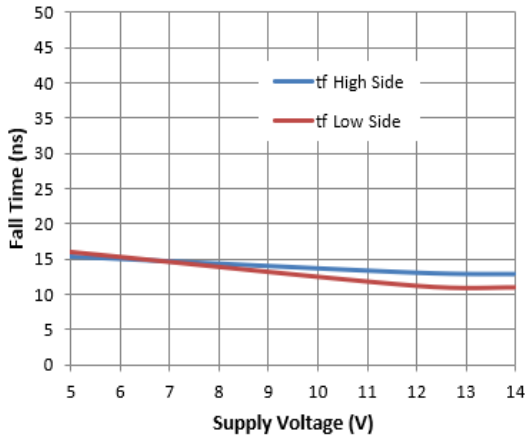


Figure 10. Fall Time vs. Supply Voltage

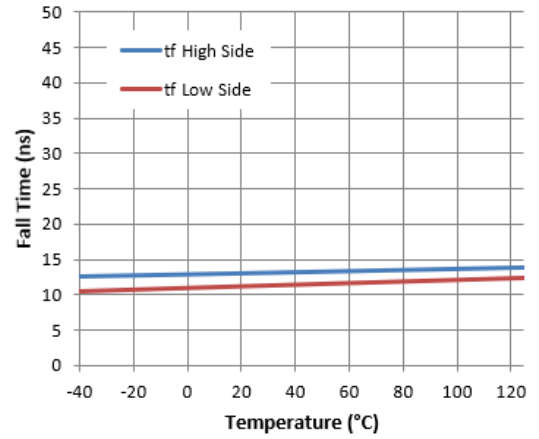


Figure 11. Fall Time vs. Temperature

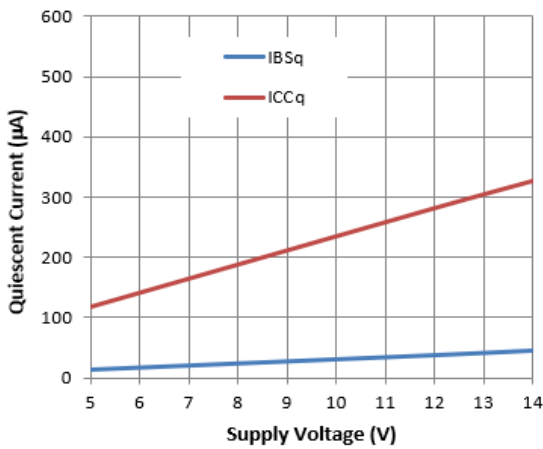


Figure 12. Quiescent Current vs. Supply Voltage

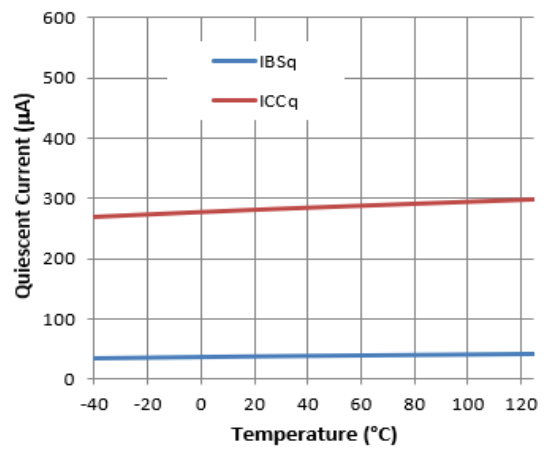


Figure 13. Quiescent Current vs. Temperature

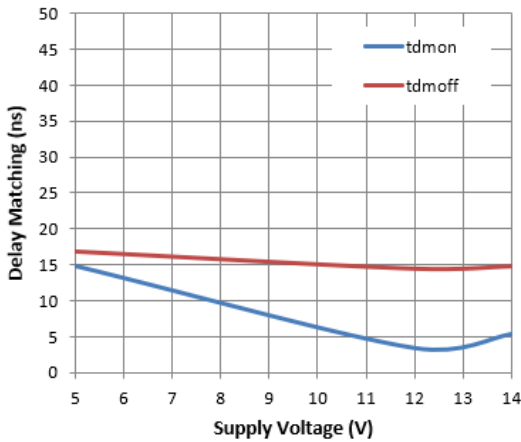


Figure 14. Delay Matching vs. Supply Voltage

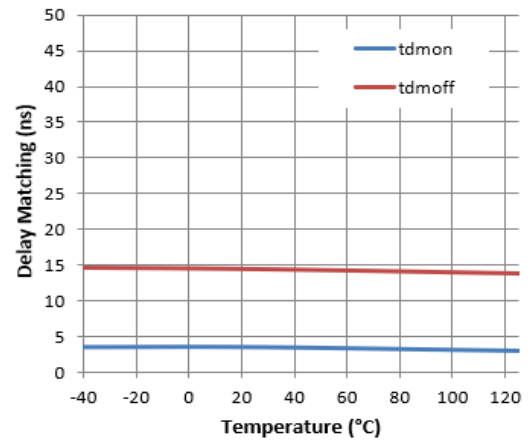


Figure 15. Delay Matching vs. Temperature



**Typical Performance Characteristics** (continued)

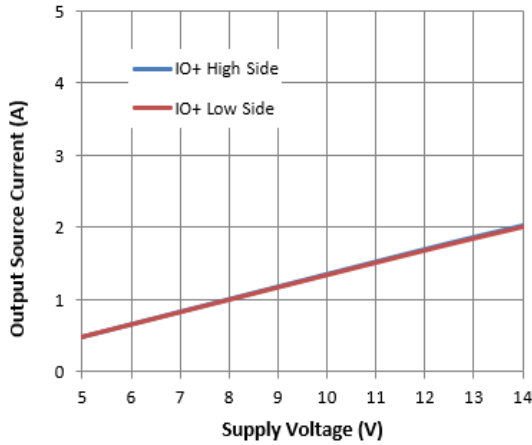


Figure 16. Output Source Current vs. Supply Voltage

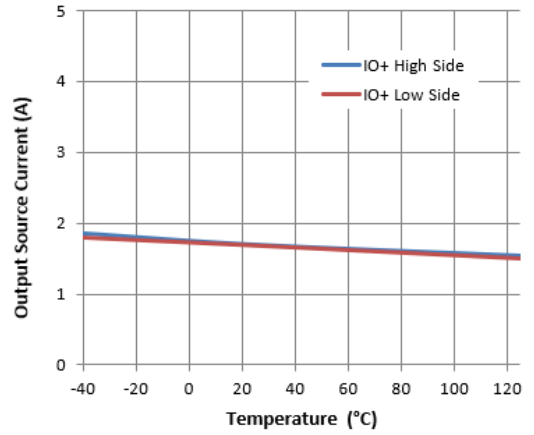


Figure 17. Output Source Current vs. Temperature

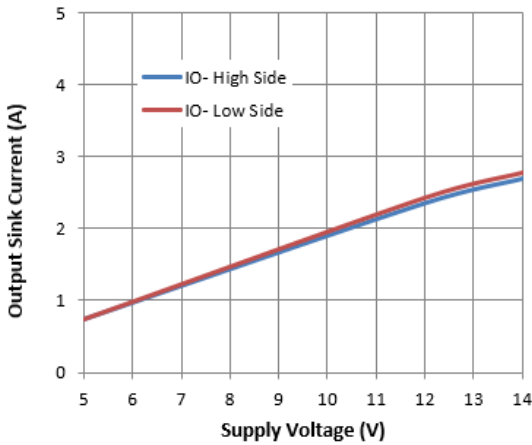


Figure 18. Output Sink Current vs. Supply Voltage

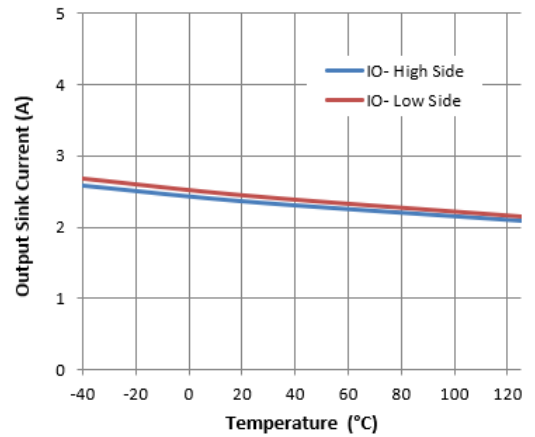


Figure 19. Output Sink Current vs. Temperature

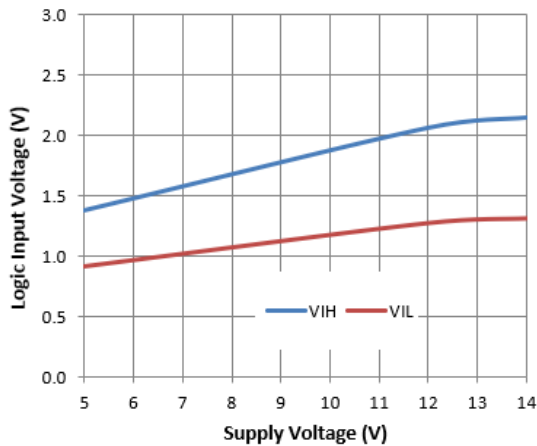


Figure 20. Logic Input Voltage vs. Supply Voltage

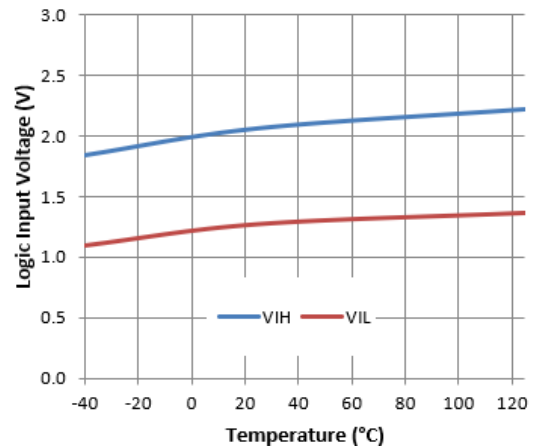


Figure 21. Logic Input Voltage vs. Temperature

**Typical Performance Characteristics** (continued)

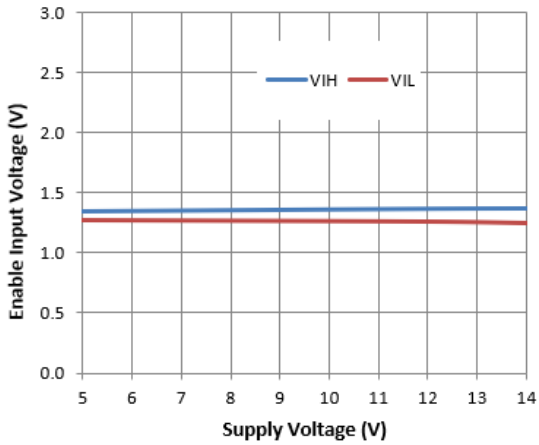


Figure 22. Enable Input Voltage vs. Supply Voltage

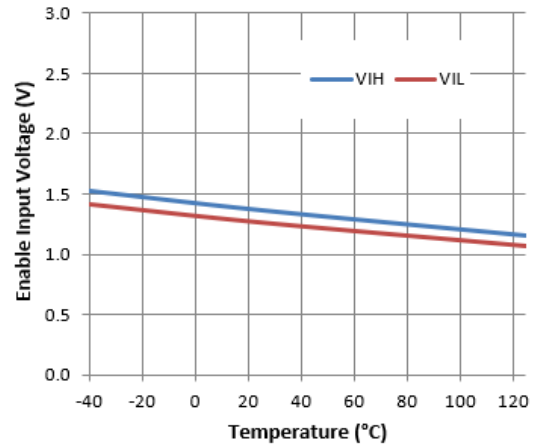


Figure 23. Enable Input Voltage vs. Temperature

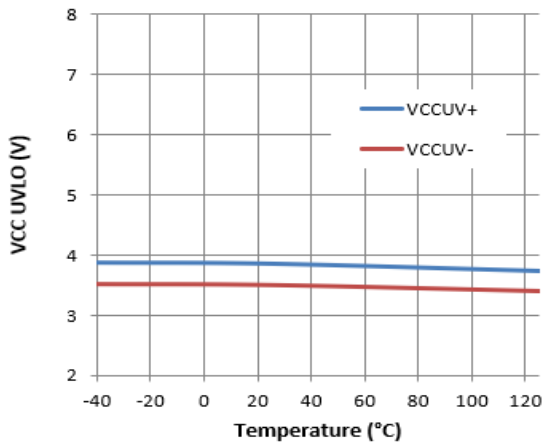


Figure 24. VCC UVLO vs. Temperature

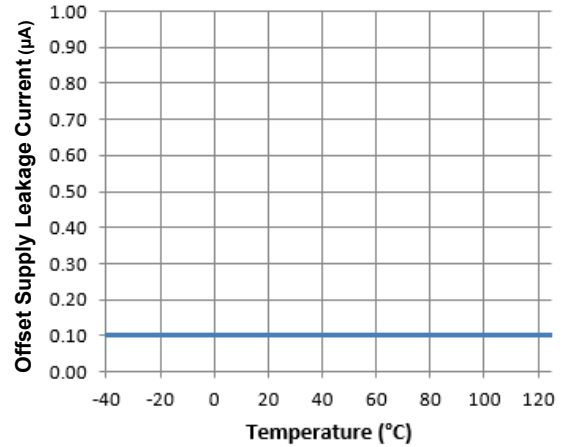


Figure 25. Offset Supply Leakage Current vs. Temperature

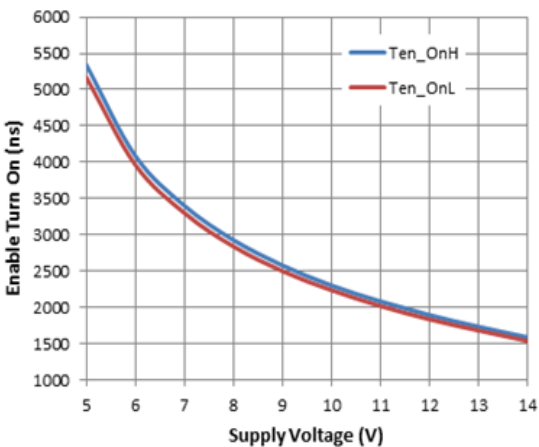


Figure 26. EN to output Ton vs. Supply Voltage

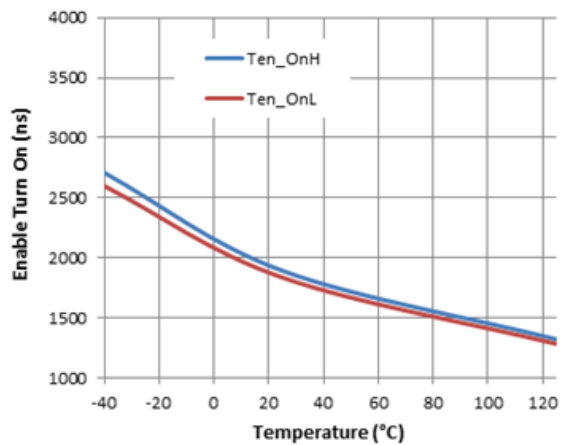
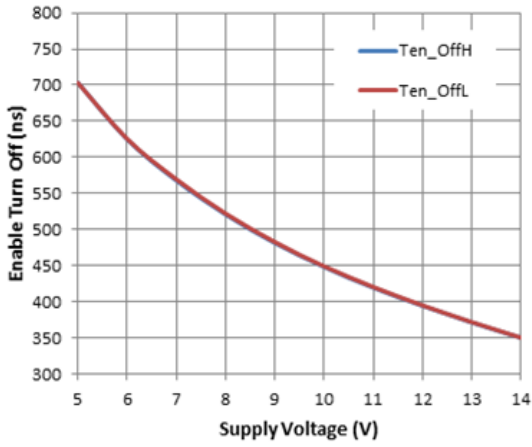
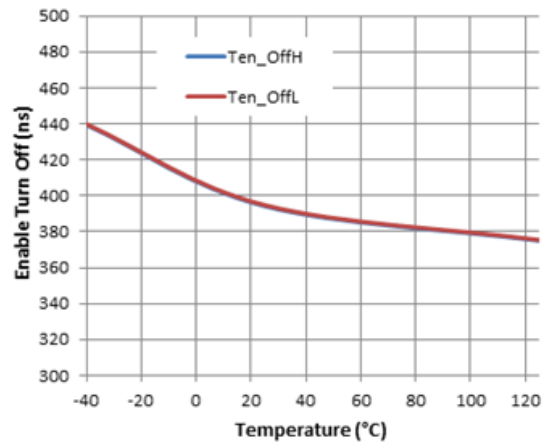


Figure 27. EN to output Ton vs. Temperature

**Typical Performance Characteristics** (continued)



**Figure 28.** EN to output Toff vs. Supply Voltage

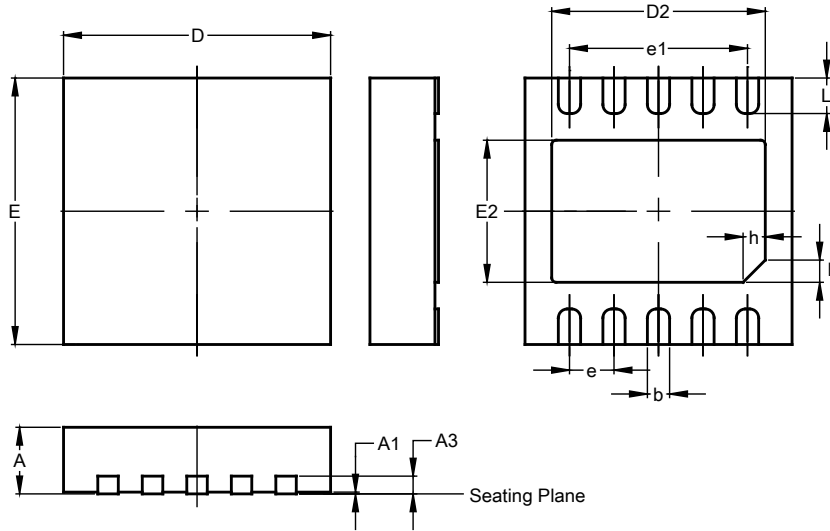


**Figure 29.** EN to output Toff vs. Temperature

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

W-DFN3030-10 (Type TH)

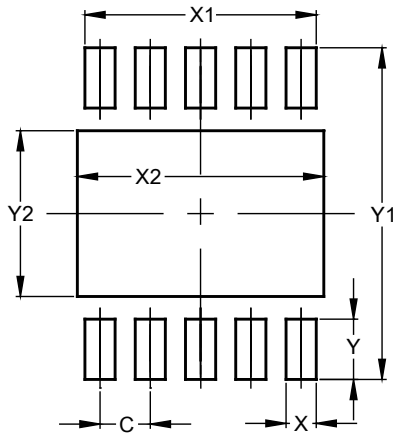


W-DFN3030-10 (Type TH)			
Dim	Min	Max	Typ
A	0.70	0.80	0.75
A1	--	0.05	0.02
A3	0.18	0.25	0.20
b	0.18	0.30	0.25
D	2.90	3.10	3.00
D2	2.40	2.60	2.50
e	0.50BSC		
e1	2.00BSC		
E	2.90	3.10	3.00
E2	1.45	1.65	1.55
h	0.20	0.30	0.25
L	0.30	0.50	0.40
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

W-DFN3030-10 (Type TH)

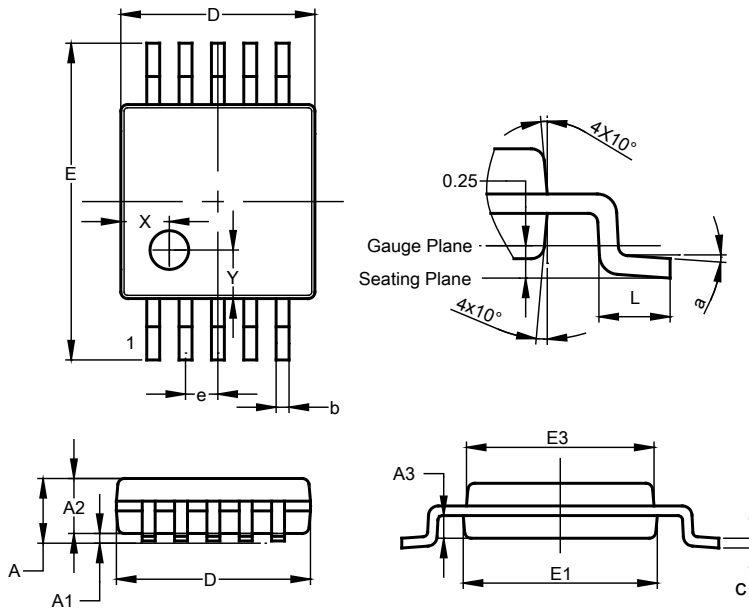


Dimensions	Value (in mm)
C	0.500
X	0.300
X1	2.300
X2	2.600
Y	0.600
Y1	3.300
Y2	1.650

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### MSOP-10

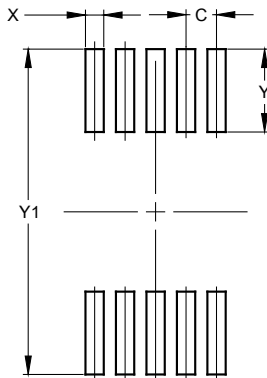


MSOP-10			
Dim	Min	Max	Typ
A	-	1.10	-
A1	0.05	0.15	0.10
A2	0.75	0.95	0.86
A3	0.29	0.49	0.39
b	0.17	0.27	0.20
c	0.08	0.23	0.15
D	2.95	3.05	3.00
e	-	-	0.50
E	4.80	5.00	4.90
E1	2.95	3.05	3.00
E3	2.85	3.05	2.95
L	0.40	0.80	0.60
X	--	--	0.750
Y	--	--	0.750
a	0°	8°	4°
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### MSOP-10



Dimensions	Value (in mm)
C	0.50
X	0.30
Y	1.35
Y1	5.30

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